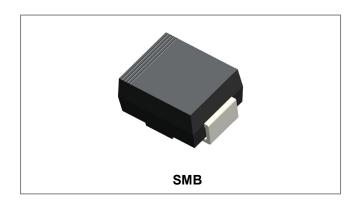






## **ER2M ULTRAFAST RECTIFIER**



#### **Features**

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



### **Mechanical Data**

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type NumberWeight: 0.09grams(approx)

### Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	ER2M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	1000	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	700	V
Average Rectified Output Current @T <sub>A</sub> = 75°C	lo	2.0	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	50.0	А
Forward Voltage @I <sub>F</sub> = 2.0A, T <sub>J</sub> =25°C	VF	1.7	V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C	I <sub>RM</sub>	5.0 50.0	μΑ
Typical Thermal Resistance Junction to Lead (Note 1)	R <sub>θJA</sub>	40	°C/W
Maximum Reverse Recovery Time (Note 2)	Trr	75	ns
Typical Junction Capacitance (Note 3)	CJ	60	pF
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

Note: 1. Mounted on P.C. Board with 8.0mm<sup>2</sup> lead area

- 2. Measured with  $I_F$ =0.5A,  $I_R$ =1.0A,  $I_{rr}$ =0.25A,
- 3. Measured at 1.0 MHZ and applied reverse voltage of 4.0  $V_{\text{DC}}$ 
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### **Ratings and Characteristics Curves**

FIG. 1- FORWARD CURRENT DERATING CURVE

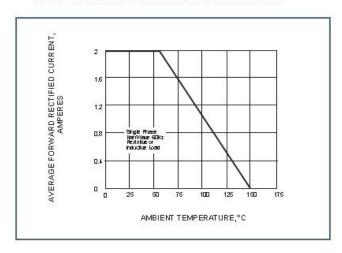


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

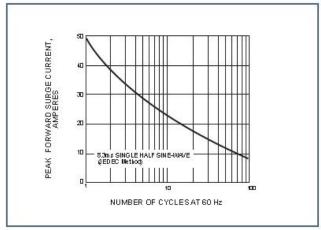


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

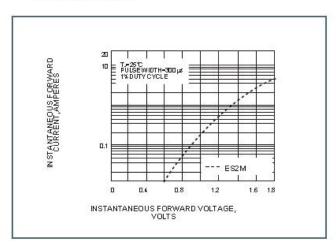
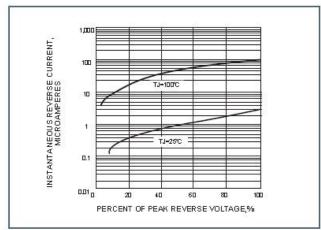


FIG. 4-TYPICAL REVERSE CHARACTERISTICS



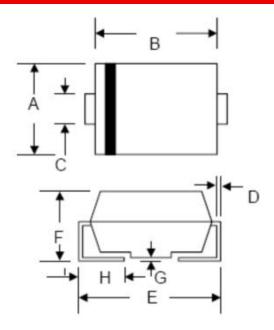
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## **Mechanical Dimensions SMB**



OVMDOL	Millimeters		Inches	
SYMBOL	Min.	Max.	Min.	Max.
Α	3.30	3.94	0.130	0.155
В	4.06	4.70	0.160	0.185
С	1.80	2.20	0.071	0.087
D	0.152	0.305	0.006	0.012
E	4.80	5.59	0.189	0.220
F	2.10	2.60	0.083	0.102
G	0.051	0.203	0.002	0.008
Н	0.76	1.52	0.030	0.060

## **Ordering Information**

Device	Package	Shipping
ER2M	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**

Where XXXXX is YYWWL

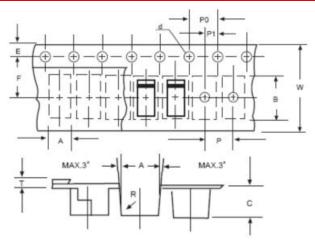
ER2M XXXXX

ER = Device Type
2 = Forward Current (2A)
M = Reverse Voltage (1000V)
YY = Year
WW = Week

= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

# **Carrier Tape Specification SMB**



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
С	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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